BFU730F

NPN wideband silicon germanium RF transistor

Rev. 1 — 29 April 2011 **Product data sheet**

1. Product profile

1.1 General description

NPN silicon germanium microwave transistor for high speed, low noise applications in a plastic, 4-pin dual-emitter SOT343F package.

CAUTION

This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

1.2 Features and benefits

- Low noise high gain microwave transistor
- Noise figure (NF) = 0.8 dB at 5.8 GHz
- High maximum power gain 18.5 dB at 5.8 GHz
- 110 GHz f_T silicon germanium technology

1.3 Applications

- 2nd LNA stage and mixer stage in DBS LNB's
- Low noise amplifiers for microwave communications systems
- Ka band oscillators DRO's
- Low current battery equipped applications
- Microwave driver / buffer applications
- Wi-Fi / WLAN / WiMAX
- GPS
- RKE
- AMR
- ZigBee
- LTE, cellular, UMTS
- SDARS first stage LNA
- FM radio
- Mobile TV
- Bluetooth

1.4 Quick reference data

Table 1. Quick reference data

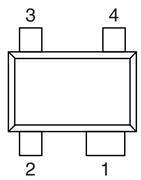
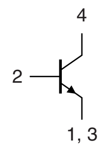
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-	10	V
V_{CEO}	collector-emitter voltage	open base		-	-	2.8	V
V_{EBO}	emitter-base voltage	open collector		-	-	1.0	V
I_C	collector current			-	5	30	mA
P_{tot}	total power dissipation	$T_{sp} \leq 90$ °C	[1]	-	-	197	mW
h_{FE}	DC current gain	I_C = 2 mA; V_{CE} = 2 V; T_j = 25 °C		205	380	555	
C_{CBS}	collector-base capacitance	V_{CB} = 2 V; f = 1 MHz		-	55	-	fF
f_T	transition frequency	I_C = 25 mA; V_{CE} = 2 V; f = 2 GHz; T_{amb} = 25 °C		-	55	-	GHz
$G_{p(max)}$	maximum power gain	I_C = 17 mA; V_{CE} = 2 V; f = 12 GHz; T_{amb} = 25 °C	[2]	-	12.5	-	dB
NF	noise figure	I_C = 5 mA; V_{CE} = 2 V; f = 12 GHz; $\Gamma_S = \Gamma_{opt}$		-	1.30	-	dB
$P_{L(1dB)}$	output power at 1 dB gain compression	I_C = 15 mA; V_{CE} = 2.5 V; $Z_S = Z_L = 50\ \Omega$; f = 5.8 GHz; T_{amb} = 25 °C		-	12.5	-	dBm

[1] T_{sp} is the temperature at the solder point of the emitter lead.

[2] $G_{p(max)}$ is the maximum power gain, if K > 1. If K < 1 then $G_{p(max)}$ = Maximum Stable Gain (MSG).

2. Pinning information

Table 2. Discrete pinning

Pin	Description	Simplified outline	Graphic symbol
1	emitter		 mbb159
2	base		
3	emitter		
4	collector		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BFU730F	-	plastic surface-mounted flat pack package; reverse pinning; 4 leads	SOT343F

4. Marking

Table 4. Marking

Type number	Marking	Description
BFU730F	D6*	* = p : made in Hong Kong
		* = t : made in Malaysia
		* = w : made in China

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	10	V
V_{CEO}	collector-emitter voltage	open base		-	2.8	V
V_{EBO}	emitter-base voltage	open collector		-	1.0	V
I_C	collector current			-	30	mA
P_{tot}	total power dissipation	$T_{sp} \leq 90$ °C	[1]	-	197	mW
T_{stg}	storage temperature			–65	+150	°C
T_j	junction temperature			-	150	°C

[1] T_{sp} is the temperature at the solder point of the emitter lead.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		304	K/W

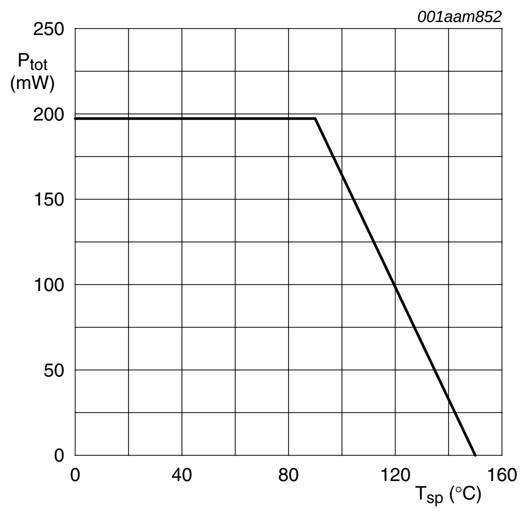


Fig 1. Power derating curve

7. Characteristics

Table 7. Characteristics

T_j = 25 °C unless otherwise specified

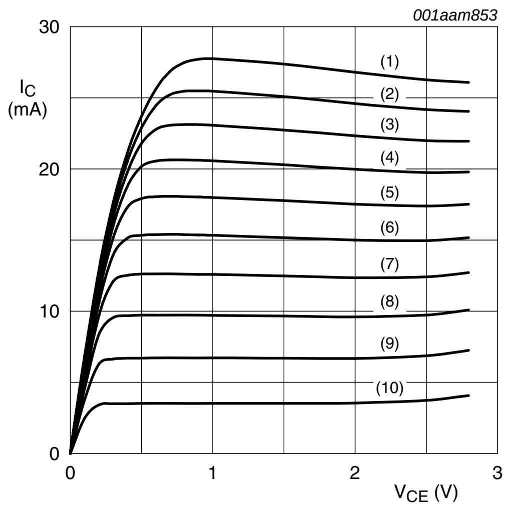
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$V_{(BR)CBO}$	collector-base breakdown voltage	I_C = 2.5 μA; I_E = 0 mA		10	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	I_C = 1 mA; I_B = 0 mA		2.8	-	-	V
I_C	collector current			-	5	30	mA
I_{CBO}	collector-base cut-off current	I_E = 0 mA; V_{CB} = 4.5 V		-	-	100	nA
h_{FE}	DC current gain	I_C = 2 mA; V_{CE} = 2 V		205	380	555	
C_{CES}	collector-emitter capacitance	V_{CB} = 2 V; f = 1 MHz		-	206	-	fF
C_{EBS}	emitter-base capacitance	V_{EB} = 0.5 V; f = 1 MHz		-	442	-	fF
C_{CBS}	collector-base capacitance	V_{CB} = 2 V; f = 1 MHz		-	55	-	fF
f_T	transition frequency	I_C = 25 mA; V_{CE} = 2 V; f = 2 GHz; T_{amb} = 25 °C		-	55	-	GHz
$G_{p(max)}$	maximum power gain	I_C = 17 mA; V_{CE} = 2 V; T_{amb} = 25 °C	[1]				
		f = 1.5 GHz		-	29	-	dB
		f = 1.8 GHz		-	28	-	dB
		f = 2.4 GHz		-	26.5	-	dB
		f = 5.8 GHz		-	18.5	-	dB
		f = 12 GHz		-	12.5	-	dB
$\|s_{21}\|^2$	insertion power gain	I_C = 17 mA; V_{CE} = 2 V; T_{amb} = 25 °C					
		f = 1.5 GHz		-	27	-	dB
		f = 1.8 GHz		-	25.5	-	dB
		f = 2.4 GHz		-	23.5	-	dB
		f = 5.8 GHz		-	16	-	dB
		f = 12 GHz		-	10.5	-	dB
NF	noise figure	I_C = 5 mA; V_{CE} = 2 V; $\Gamma_S = \Gamma_{opt}$; T_{amb} = 25 °C					
		f = 1.5 GHz		-	0.50	-	dB
		f = 1.8 GHz		-	0.50	-	dB
		f = 2.4 GHz		-	0.55	-	dB
		f = 5.8 GHz		-	0.80	-	dB
		f = 12 GHz		-	1.30	-	dB
G_{ass}	associated gain	I_C = 5 mA; V_{CE} = 2 V; $\Gamma_S = \Gamma_{opt}$; T_{amb} = 25 °C					
		f = 1.5 GHz		-	25.0	-	dB
		f = 1.8 GHz		-	23.5	-	dB
		f = 2.4 GHz		-	21.5	-	dB
		f = 5.8 GHz		-	15.0	-	dB
		f = 12 GHz		-	11.0	-	dB

Table 7. Characteristics *...continued*

T_j = 25 °C unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$P_{L(1dB)}$	output power at 1 dB gain compression	I_C = 15 mA; V_{CE} = 2.5 V; $Z_S = Z_L$ = 50 Ω; T_{amb} = 25 °C				
		f = 1.5 GHz	-	12.5	-	dBm
		f = 1.8 GHz	-	12	-	dBm
		f = 2.4 GHz	-	11.5	-	dBm
		f = 5.8 GHz	-	12.5	-	dBm
IP3	third-order intercept point	I_C = 20 mA; V_{CE} = 2.5 V; $Z_S = Z_L$ = 50 Ω; T_{amb} = 25 °C				
		f = 1.5 GHz	-	26.5	-	dBm
		f = 1.8 GHz	-	26.5	-	dBm
		f = 2.4 GHz	-	26.5	-	dBm
		f = 5.8 GHz	-	29	-	dBm

[1] $G_{p(max)}$ is the maximum power gain, if K > 1. If K < 1 then $G_{p(max)}$ = MSG.



T_{amb} = 25 °C.

(1) I_B = 100 μA

(2) I_B = 90 μA

(3) I_B = 80 μA

(4) I_B = 70 μA

(5) I_B = 60 μA

(6) I_B = 50 μA

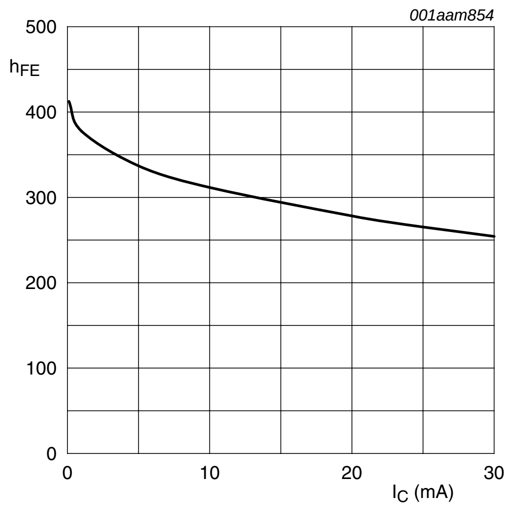
(7) I_B = 40 μA

(8) I_B = 30 μA

(9) I_B = 20 μA

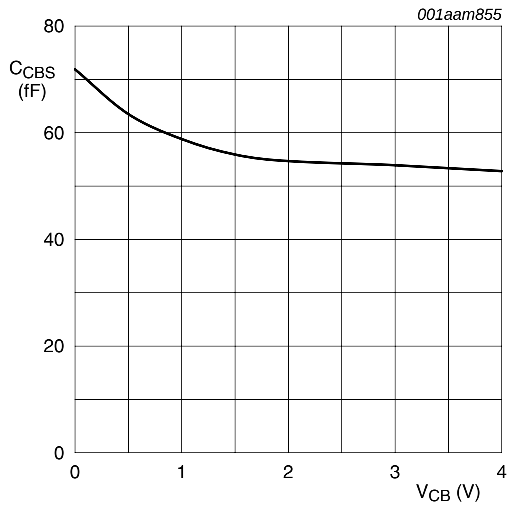
(10) I_B = 10 μA

Fig 2. Collector current as a function of collector-emitter voltage; typical values



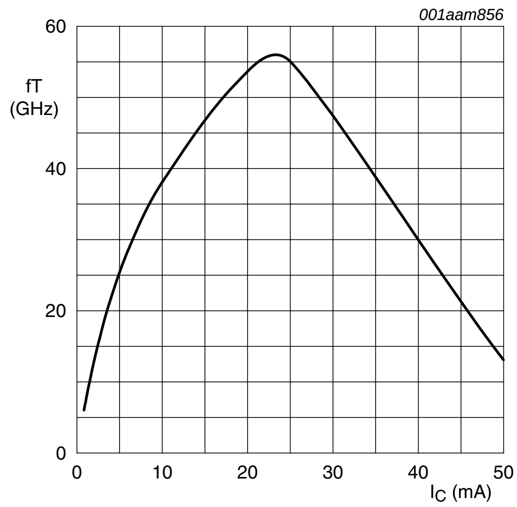
V_{CE} = 2 V; T_{amb} = 25 °C.

Fig 3. DC current gain as a function of collector current; typical values



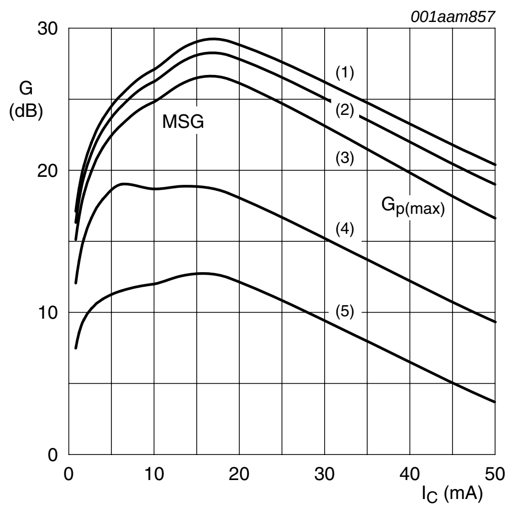
f = 1 MHz, T_{amb} = 25 °C.

Fig 4. Collector-base capacitance as a function of collector-base voltage; typical values



V_{CE} = 2 V; f = 2 GHz; T_{amb} = 25 °C.

Fig 5. Transition frequency as a function of collector current; typical values



V_{CE} = 2 V; T_{amb} = 25 °C.

(1) f = 1.5 GHz

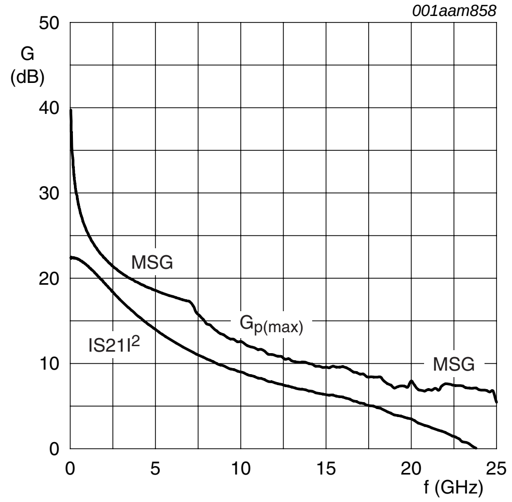
(2) f = 1.8 GHz

(3) f = 2.4 GHz

(4) f = 5.8 GHz

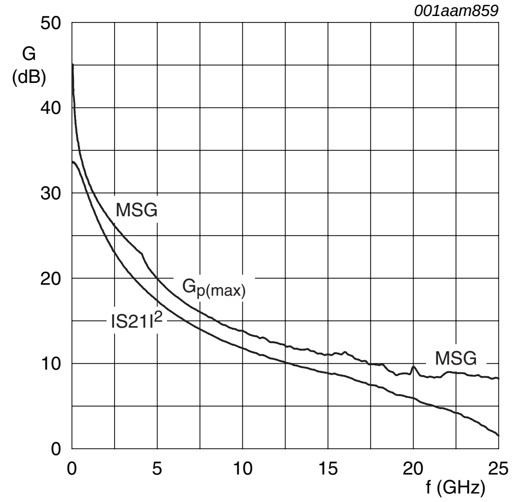
(5) f = 12 GHz

Fig 6. Gain as a function of collector current; typical value



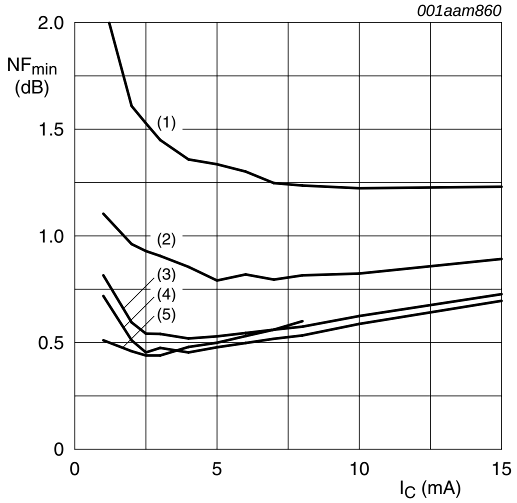
V_{CE} = 2 V; I_C = 5 mA; T_{amb} = 25 °C.

Fig 7. Gain as a function of frequency; typical values



V_{CE} = 2 V; I_C = 17 mA; T_{amb} = 25 °C.

Fig 8. Gain as a function of frequency; typical values



V_{CE} = 2 V; T_{amb} = 25 °C.

(1) f = 12 GHz

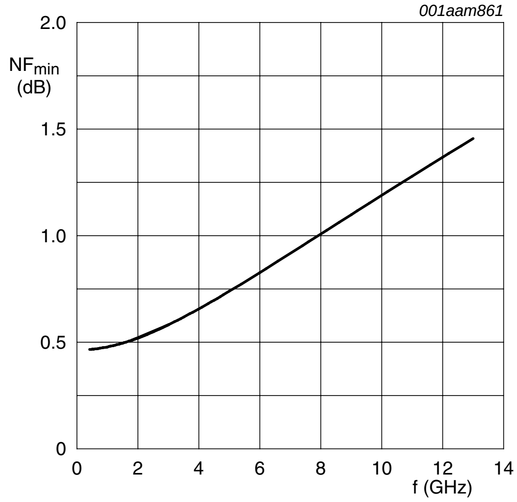
(2) f = 5.8 GHz

(3) f = 2.4 GHz

(4) f = 1.8 GHz

(5) f = 1.5 GHz

Fig 9. Minimum noise figure as a function of collector current; typical values

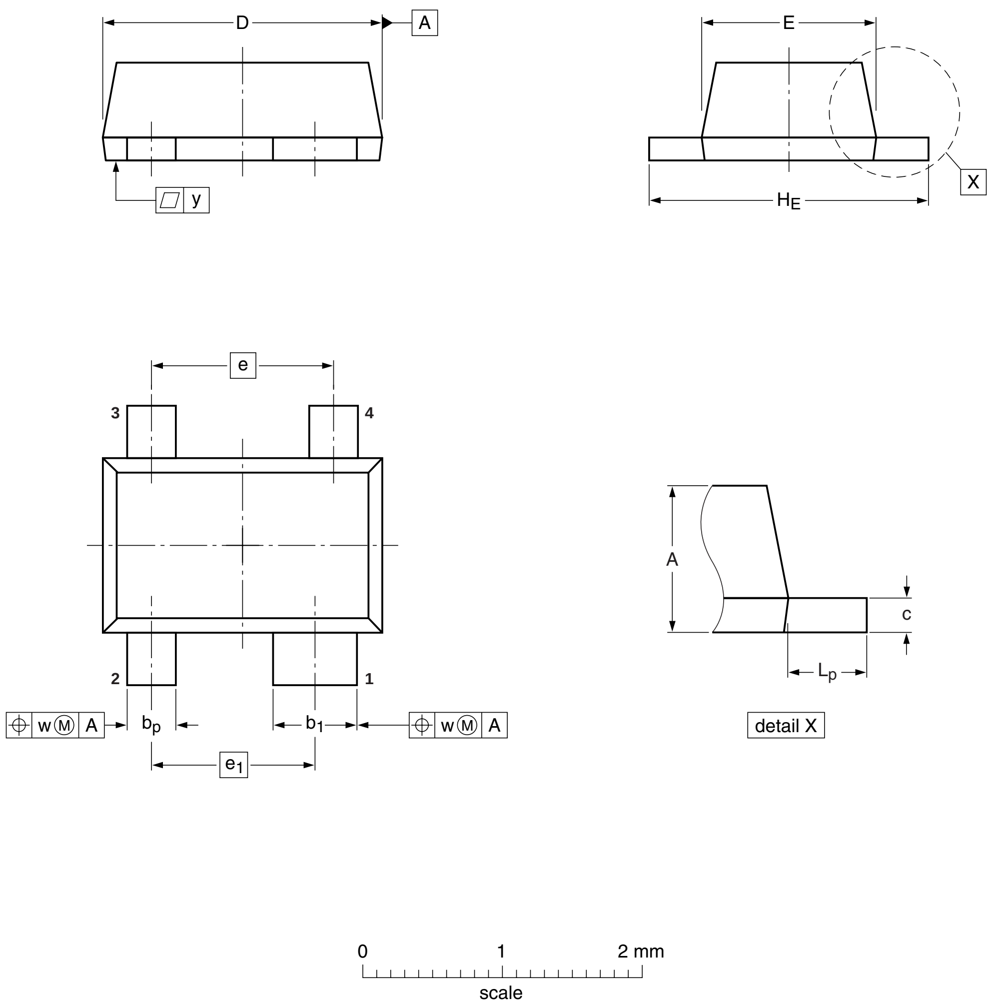


I_C = 5 mA; V_{CE} = 2 V; T_{amb} = 25 °C.

Fig 10. Minimum noise figure as a function of frequency; typical values

8. Package outline

Plastic surface-mounted flat pack package; reverse pinning; 4 leads **SOT343F**



DIMENSIONS (mm are the original dimensions)

UNIT	A max	b_p	b_1	c	D	E	e	e_1	H_E	L_p	w	y
mm	0.75 0.65	0.4 0.3	0.7 0.5	0.25 0.10	2.2 1.8	1.35 1.15	1.3	1.15	2.2 2.0	0.48 0.38	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT343F						~~05-07-12~~ 06-03-16

Fig 11. Package outline SOT343F

9. Abbreviations

Table 8. Abbreviations

Acronym	Description
AMR	Automatic Meter Reading
DBS	Direct Broadcast Satellite
DC	Direct Current
DRO	Dielectric Resonator Oscillator
FM	Frequency Modulation
GPS	Global Positioning System
Ka	Kurtz above
LNA	Low Noise Amplifier
LNB	Low Noise Block
LTE	Long Term Evolution
NPN	Negative-Positive-Negative
RF	Radio Frequency
RKE	Remote Keyless Entry
SDARS	Satellite Digital Audio Radio Service
UMTS	Universal Mobile Telecommunications System
WiMAX	Worldwide Interoperability for Microwave Access
WLAN	Wireless Local Area Network

10. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BFU730F v.1	20110429	Product data sheet	-	-

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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For more information, please visit: **http://www.nxp.com**

For sales office addresses, please send an email to: **salesaddresses@nxp.com**

13. Contents

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